

Isc N-Channel MOSFET Transistor

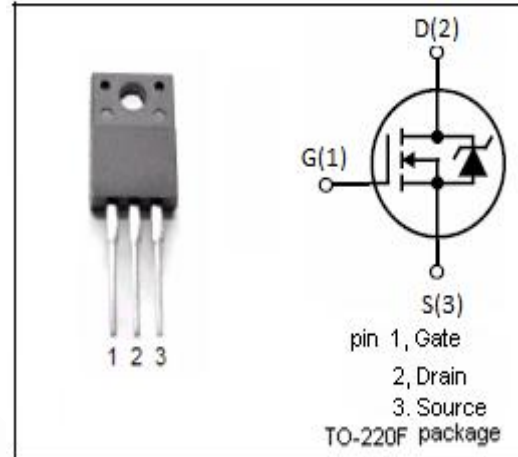
SPA08N80C3

• FEATURES

- With TO-220F package
- Low input capacitance and gate charge
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

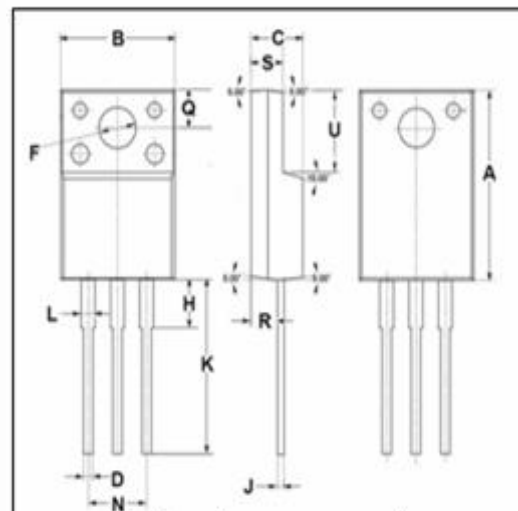
• APPLICATIONS

- Switching applications



• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	800	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous @T _c =25°C (V _{GS} at 10V) T _c =100°C	8 5.1	A
I _{DM}	Drain Current-Single Pulsed	24	A
P _D	Total Dissipation @T _c =25°C	40	W
T _j	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



DIM	mm	
	MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	3.8	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	80	°C/W

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	800			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =0.47mA	2.1		3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =5.1A		560	650	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 800V; V _{GS} = 0V; T _J =25°C V _{DS} = 800V; V _{GS} = 0V; T _J =150°C			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =8A, V _{GS} = 0V		1.0	1.2	V